

128Kx8 Bit Static RAM

FEATURES

- Fast Access Time 70,85,100,120 ns (max.)
- Low Power Dissipation
 - Standby (CMOS): 10µW (typ.) L-Version
 - 5µW (typ.) LL-Version
 - Operating : 35mW (typ.)
- Single 5V ± 10% Power Supply
- TTL compatible inputs and outputs
- Fully Static Operation
 - No clock or refresh required
- Three State Outputs
- Battery Back-up Operation
 - 2V(min.) Data Retention
- Standard Pin Configuration
 - KM681000ALP/ALP-L : 32 pin-DIP (600mil)
 - KM681000ALG/ALG-L : 32 pin-SOP (525mil)
 - KM681000ALT/ALT-L : 32 pin-TSOP (Standard Type)
 - KM681000ALR/ALR-L : 32 pin-TSOP (Reverse Type)

GENERAL DESCRIPTION

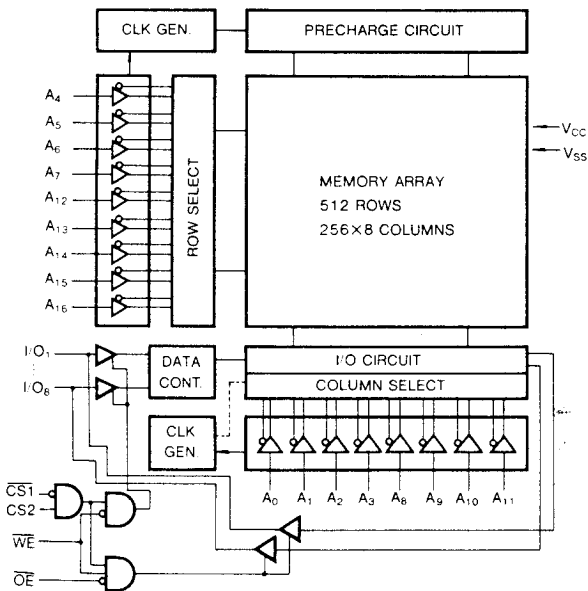
The KM681000AL/AL-L is a 1,048,576-bit high-speed Static Random Access Memory organized as 131,072 words by 8 bits.

The device is fabricated using Samsung's advanced CMOS process.

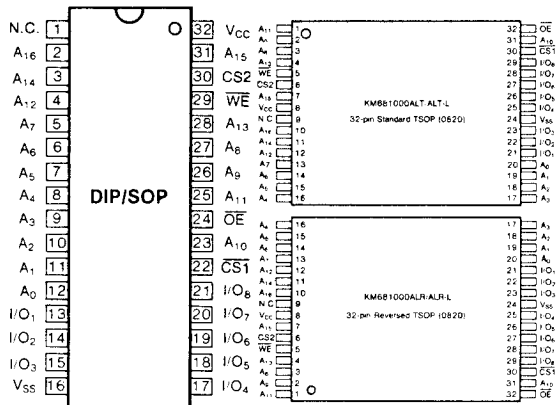
The KM681000AL/AL-L has an output enable input for precise control of the data outputs. It also has a chip enable input for the minimum current power down mode.

The KM681000AL/AL-L has been designed for high speed and low power applications. It is particularly well suited for battery back-up nonvolatile memory application.

FUNCTIONAL BLOCK DIAGRAM



PIN CONFIGURATION (TOP VIEW)



Pin Name	Pin Function
A0-A16	Address Inputs
WE	Write Enable Input
CS1, CS2	Chip Select Inputs
OE	Output Enable Input
I/O1-I/O8	Data Input/Outputs
Vcc	Power (+ 5V)
Vss	Ground
N.C.	No Connection